

Future Directions in Hybridization of Pixel Detectors

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Research Center of
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Outline

- **Introduction**
- **Wafer Bumping and Flip Chip Bonding for ATLAS**
- **Future Options and Requirements:**
 - **Bump size and Pitch**
 - **Lead Free Bumping**
 - **Thin Silicon**
 - **Integration of Passives**
 - **3D Integration**

Joseph von Fraunhofer (1787 - 1826)



Researcher

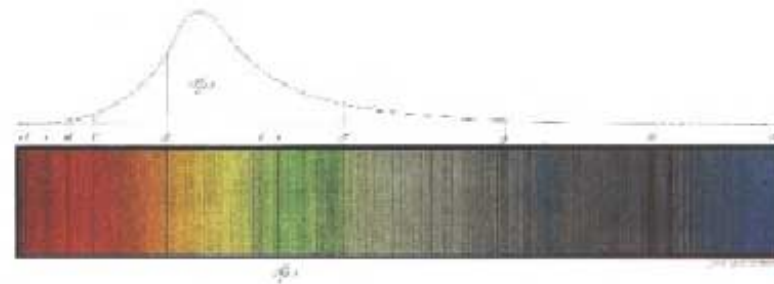
discovery of "Fraunhofer Lines"
in the sun's spectrum

Inventor

new methods of lens processing

Entrepreneur

head of royal glass factory



Fraunhofer in profile

56
institutes



Materials and components

Production technology

Information and communication

9500
employees
(full-time
equivalence)



Microelectronics and microsystems

Sensor systems, testing technologies

Process engineering

Energy, construction, environment, health

900 million Euro
budget



Technical and economic studies

Fraunhofer Institut for Reliability and Microintegration IZM



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Microperipheric Technologies



- **220 Scientists and Engineers (+100 Students)/ Cleanroom 800 m²**
- **Applied Research and Development of Advanced Packaging Solutions for Microelectronics**
- **Branch Labs and Centers in Chemnitz, Teltow, Paderborn, Oberpfaffenhofen and Munich**
- **Worldwide Technology Transfer and Consulting Services**



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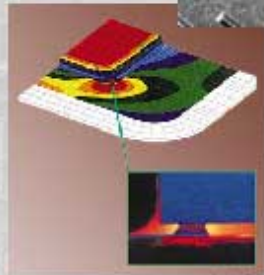
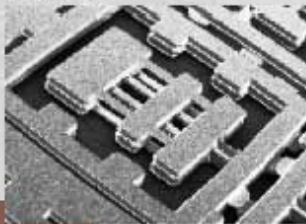
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Material Development and Simulation

Micro Devices and Equipment



Mechanical Reliability and Micro Materials



Polymeric Materials and Composites

High Density Interconnect & Waferlevel Packaging



Chip Interconnection Technologies



Board Interconnection Technologies

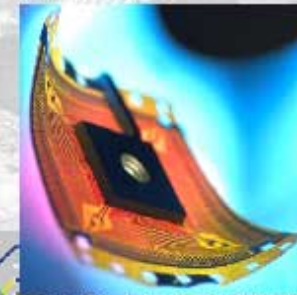


Packaging Technologies

Packaging for Microelectronics / Microsystems and Mechatronics

System Integration

Pervasive Computing System Technologies



Advanced System Engineering



Environmental Engineering



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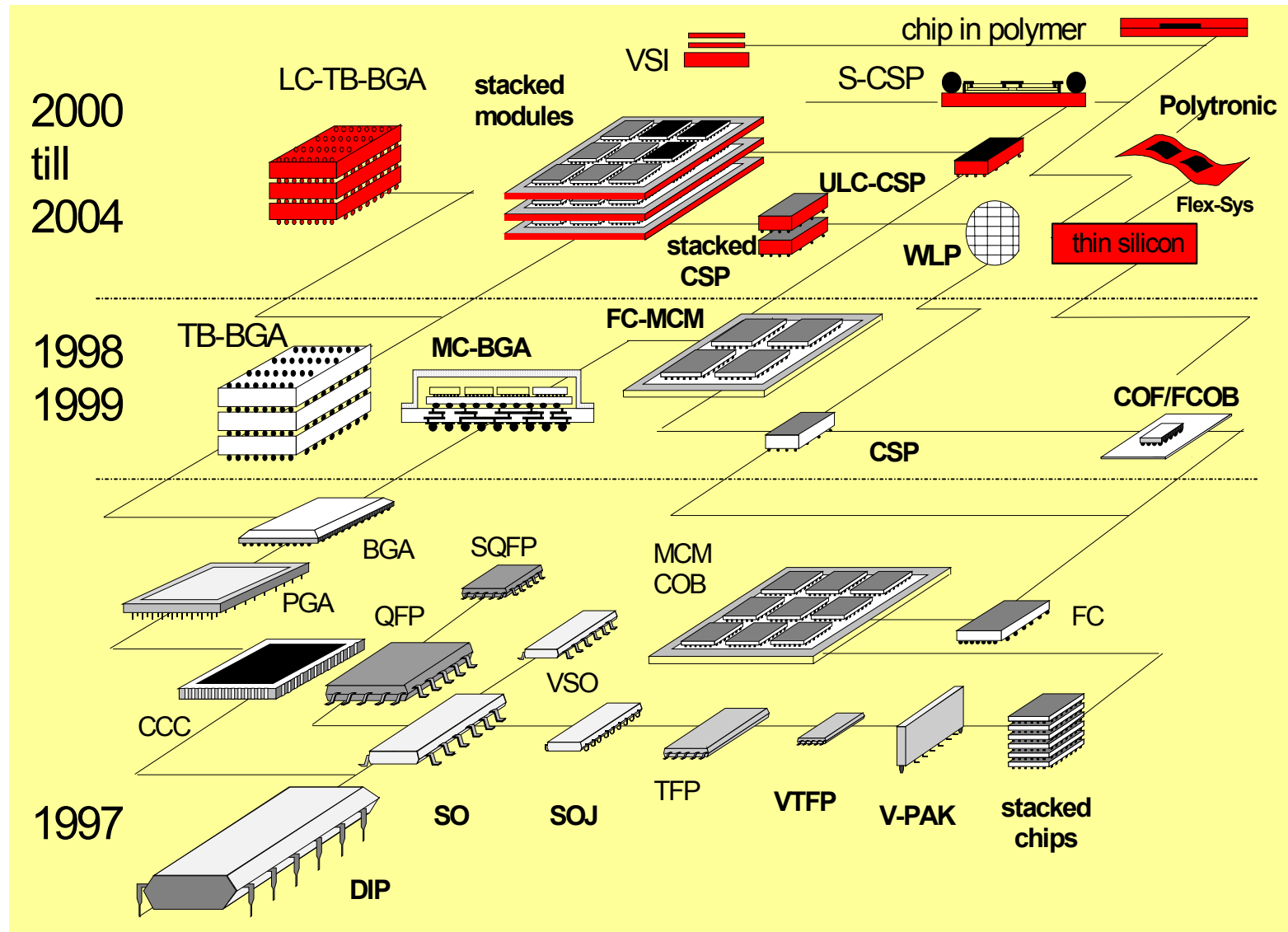
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Packaging Roadmap



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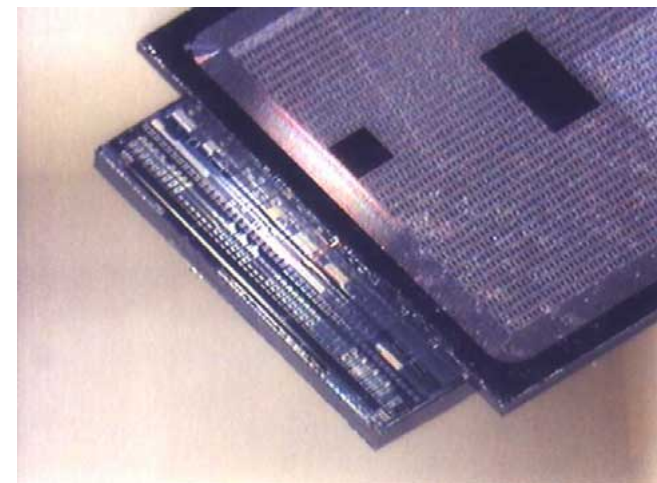
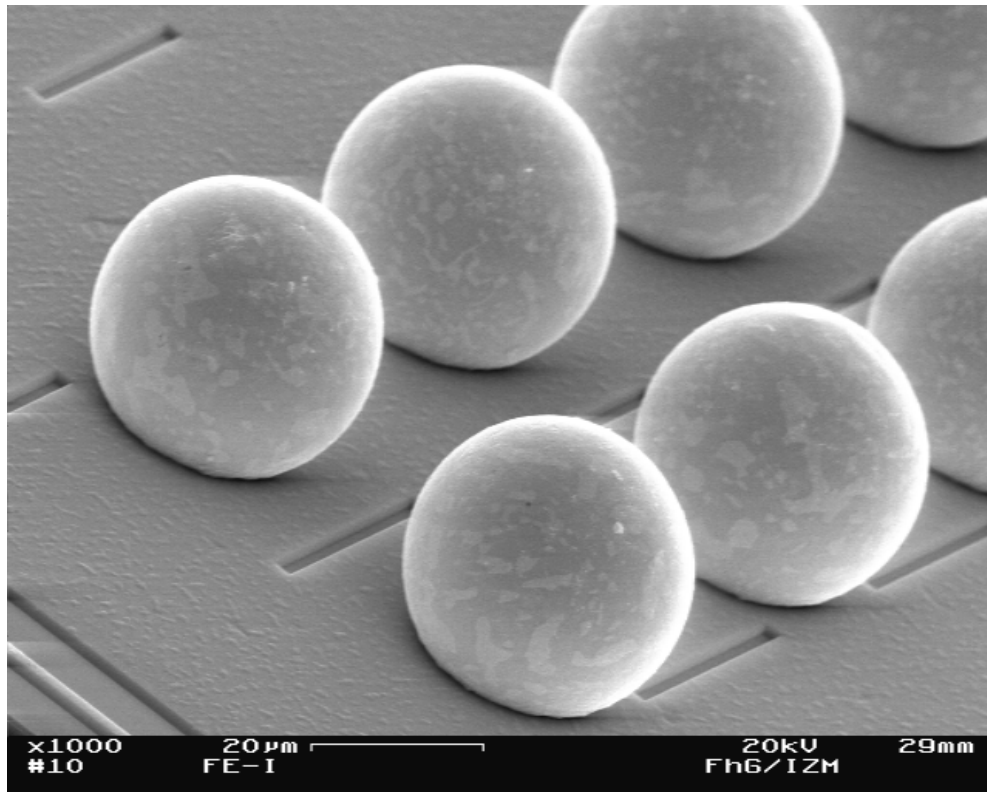
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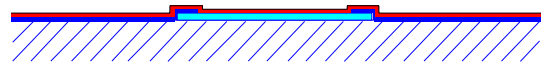
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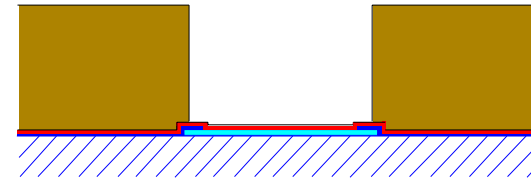
Wafer Bumping and Flip Chip Bonding for ATLAS



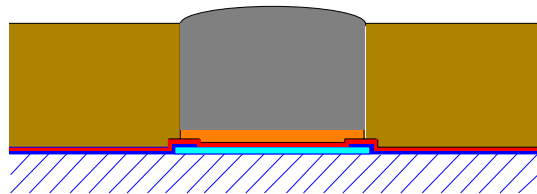
Processflow PbSn-Bumping using Electroplating



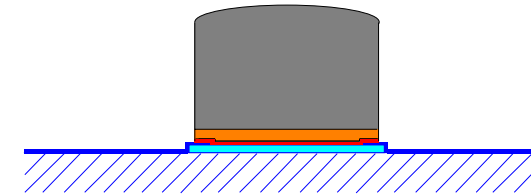
Sputter Etching and Sputtering of the Plating Base / UBM



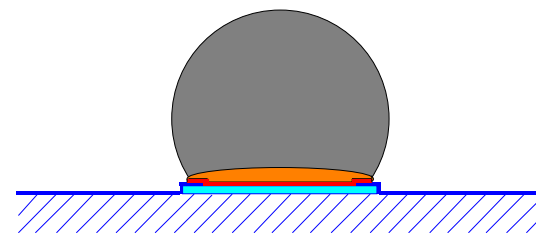
Spin Coating and Printing of Photoresist



Electroplating of Cu and PbSn

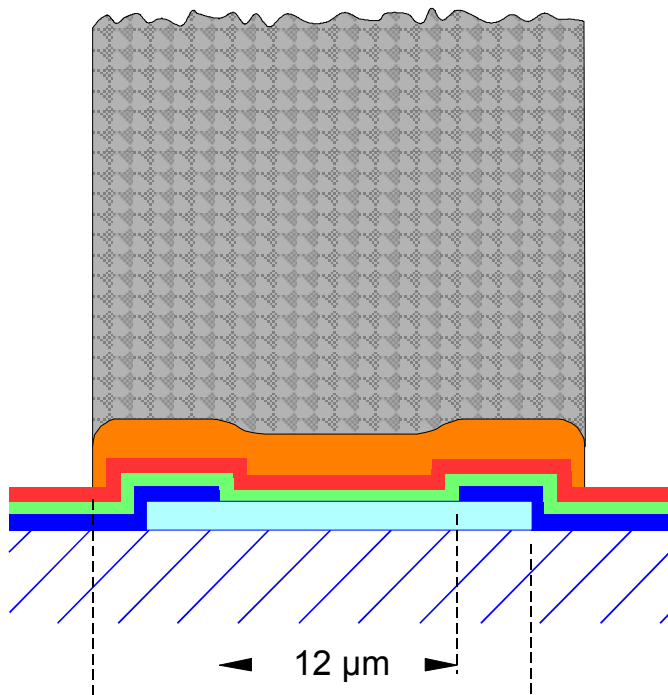


Resist Stripping and wet Etching of the Plating Base



Reflow

Fundamental Construction of Bumps on ATLAS Detector Chips



as plated

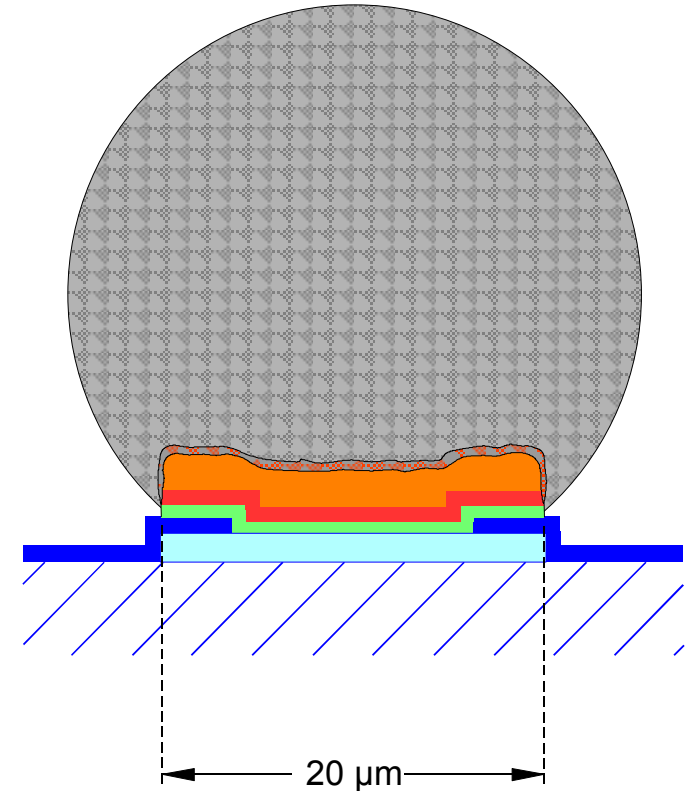
25 μm electroplated PbSn63

5 μm electroplated Cu
as solderable base

300 nm sputtered Cu
as plating base

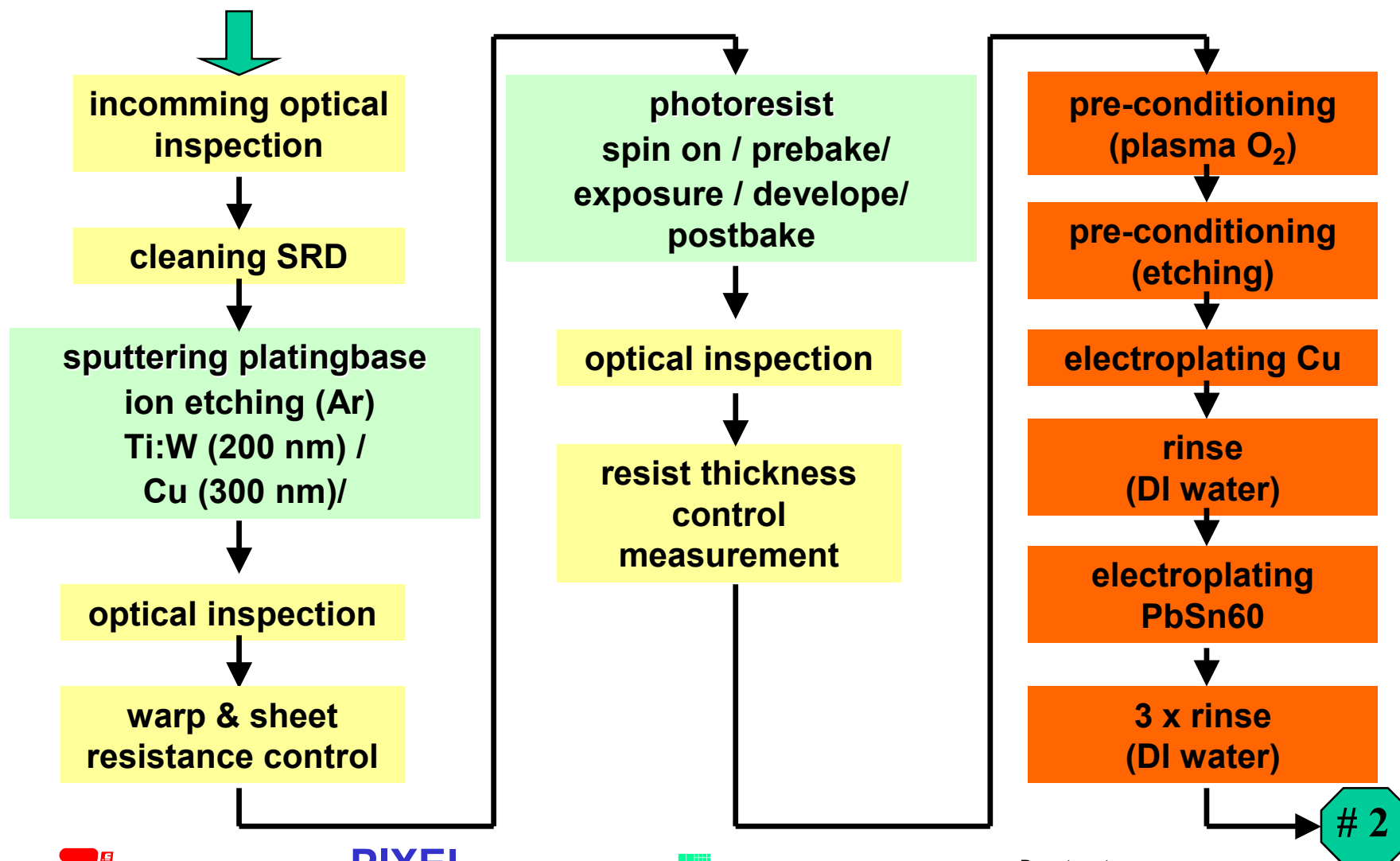
200 nm sputtered Ti:W
as adhesion layer
and diffusion barrier

Al chip pad with
overlapped passivation

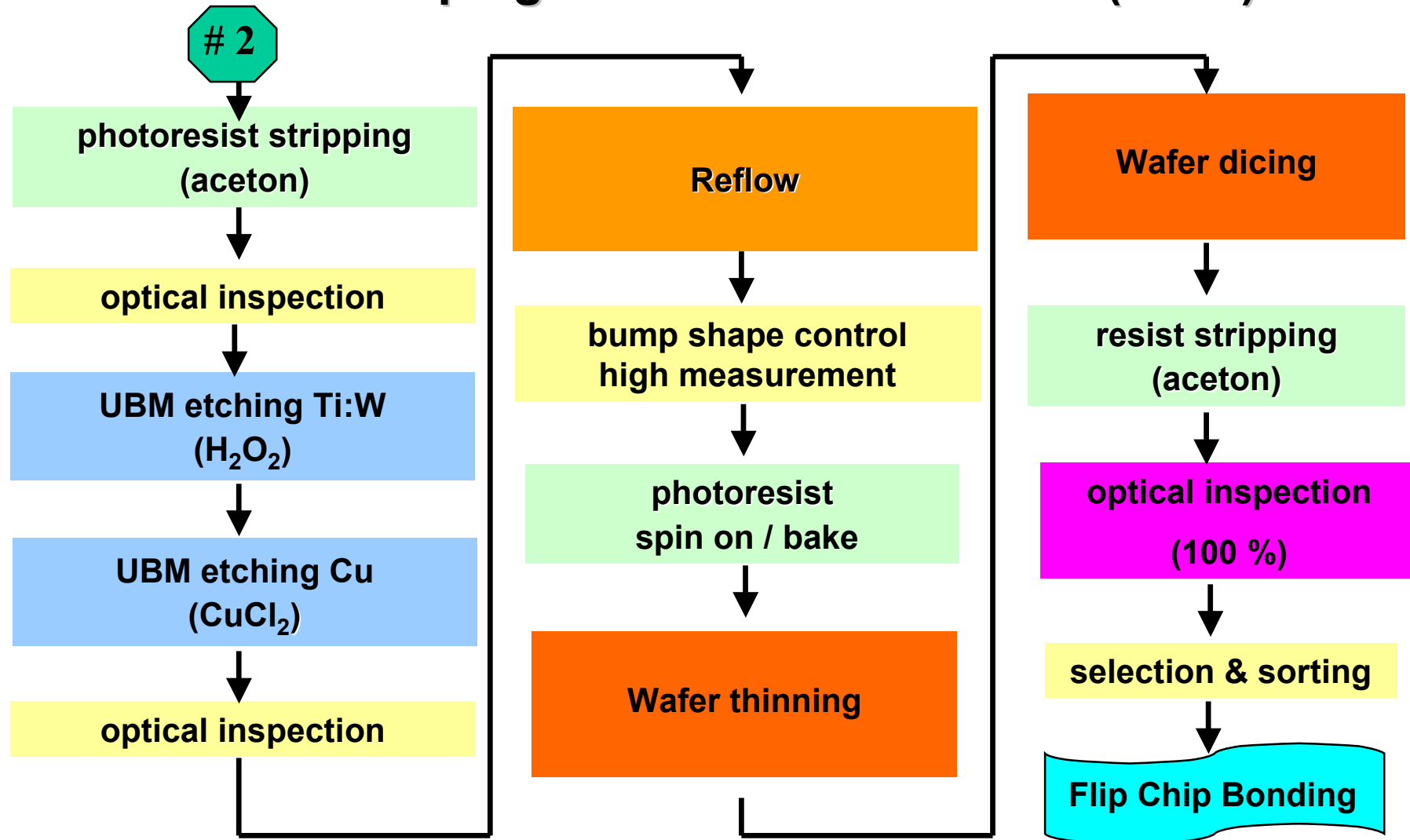


after reflow

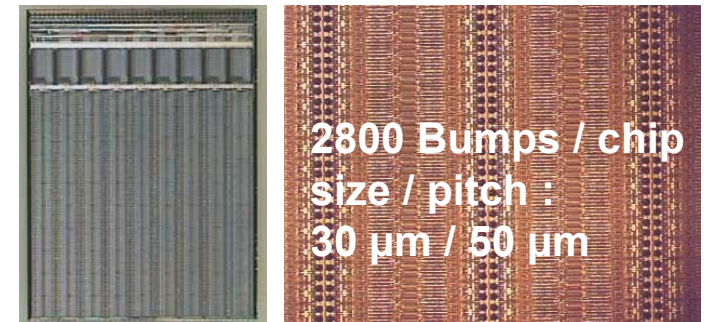
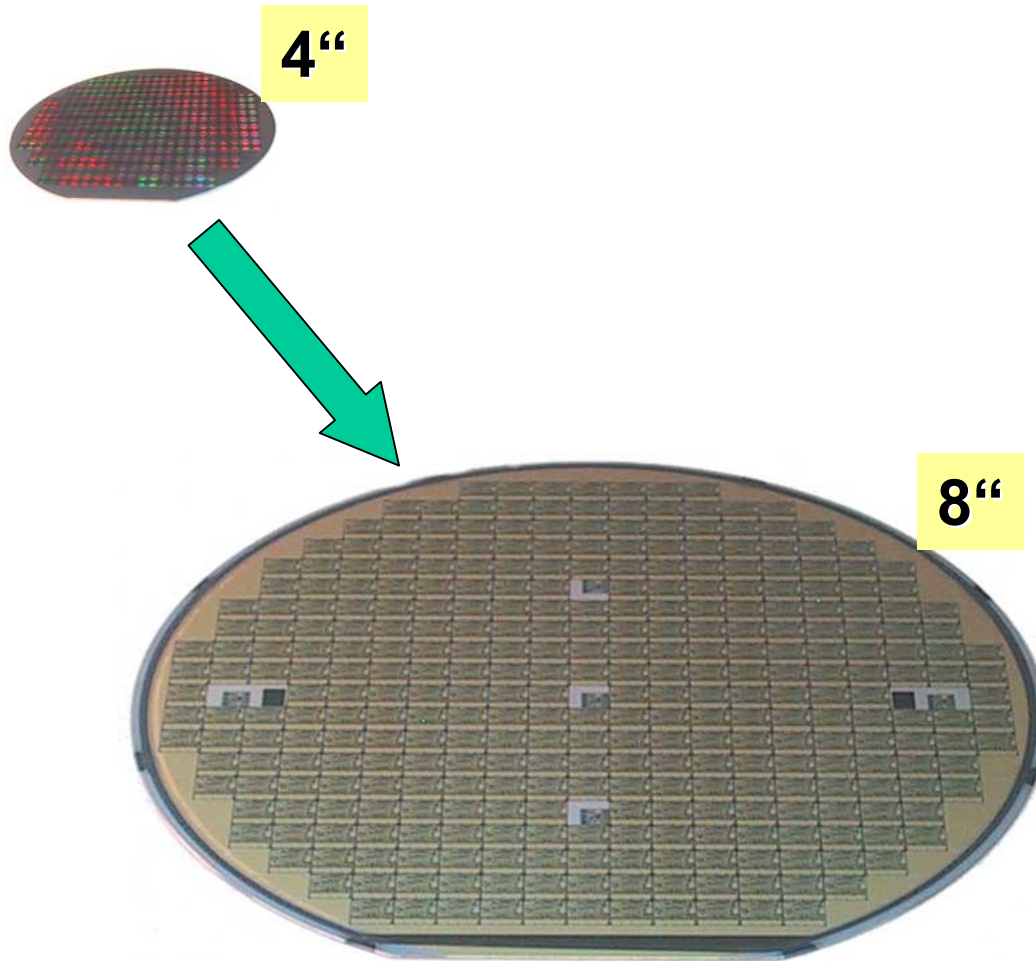
PbSn Bumping Process Flow in Detail



PbSn Bumping Process Flow in Detail (cont.)



High Density ECD Bumping & Flip Chip IBM 0.25 μm rad tolerant design





Cleanroom 800 sqm



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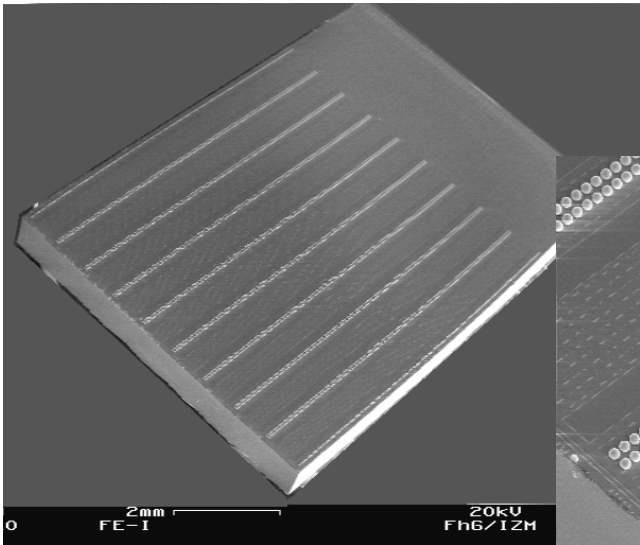
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Electroplating Equipment Semitool Equinox

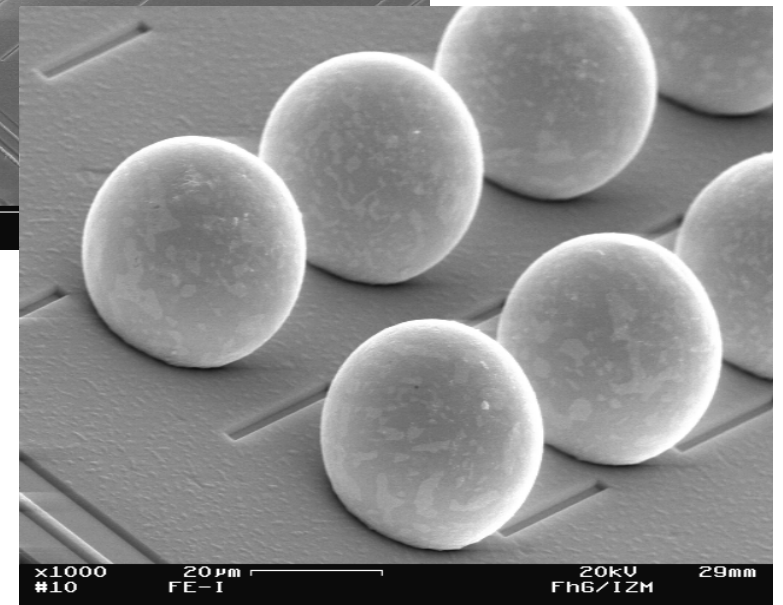
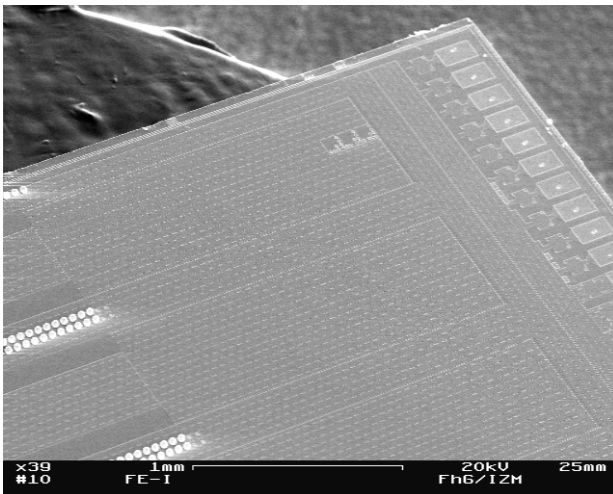
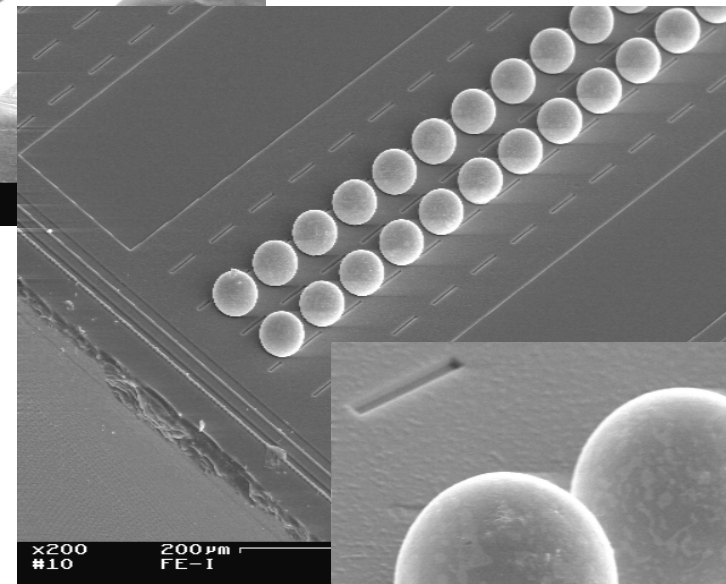
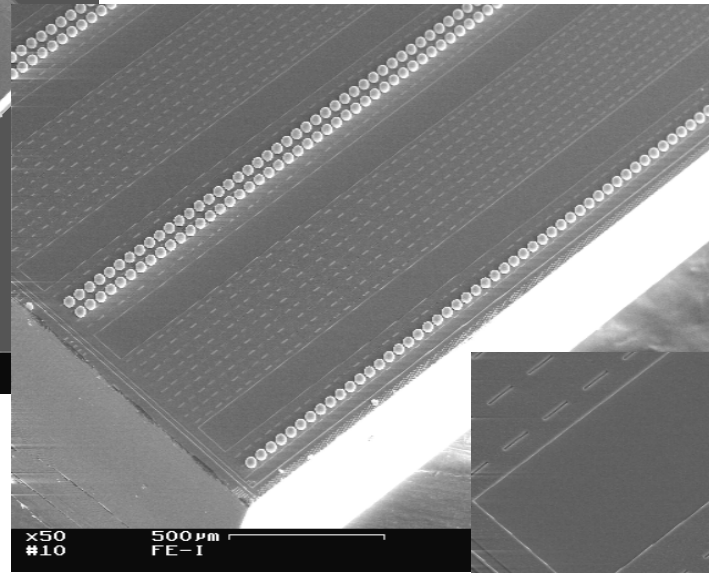


Bumped FE-I Chip

IBM 0.25 μm rad tolerant design



Chip with 9 column pairs



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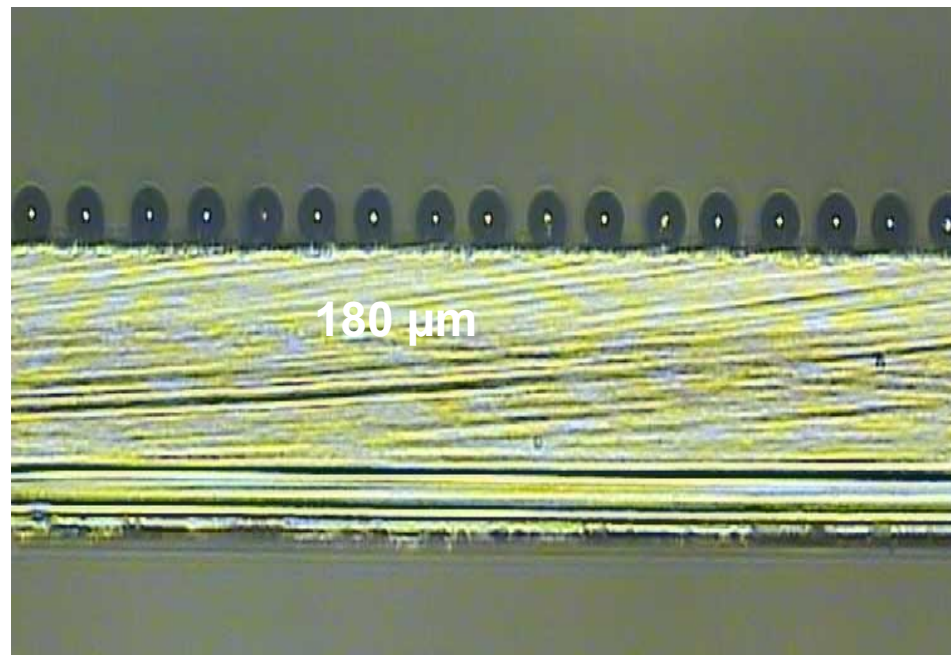
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Thinning of bumped FE - I wafers:

development of resistlayers to protect the bumps from damage during the grinding and etching process



Optical Bump Inspection

Automated Defect Inspection System NSX-90 August Technology



Inspection time:

ATLAS FE-I [8“]

bump size: 20 μ m

pitch: 50 μ m

\approx 120 min / wafer all bumps



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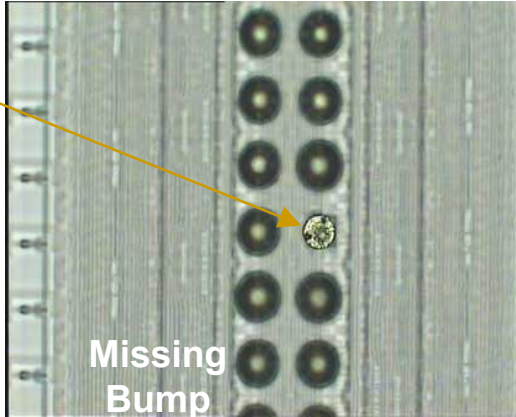
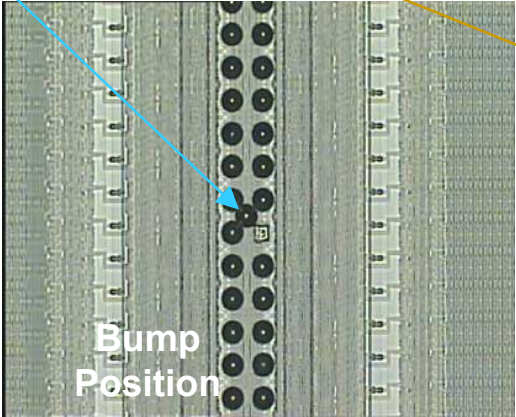
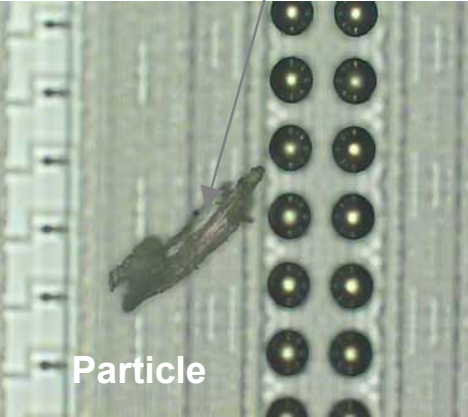
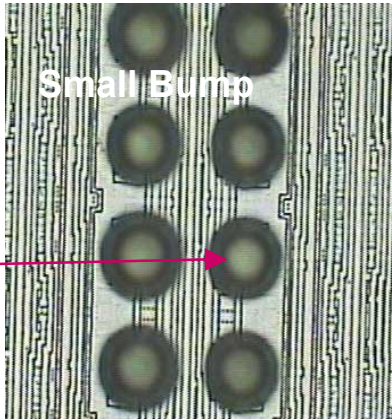
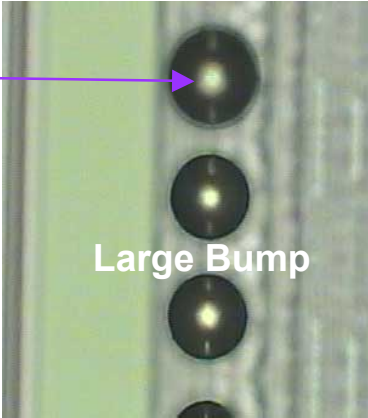
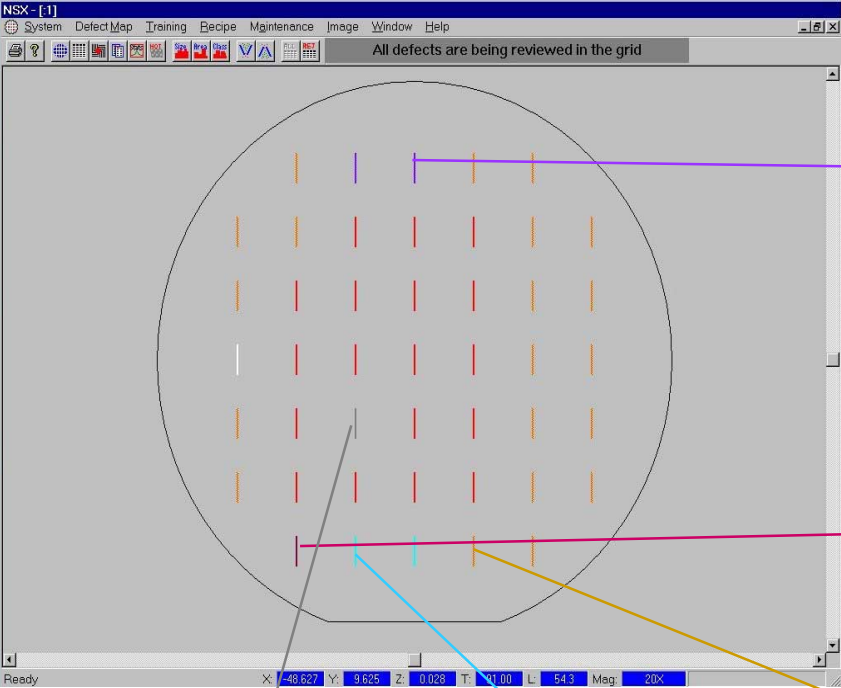
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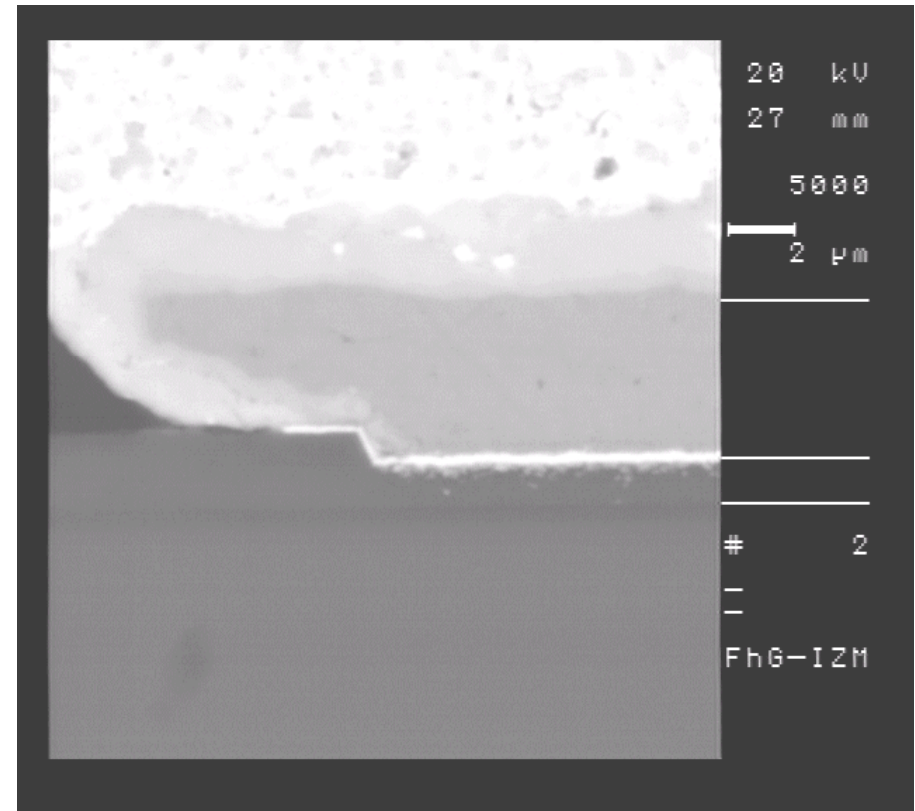
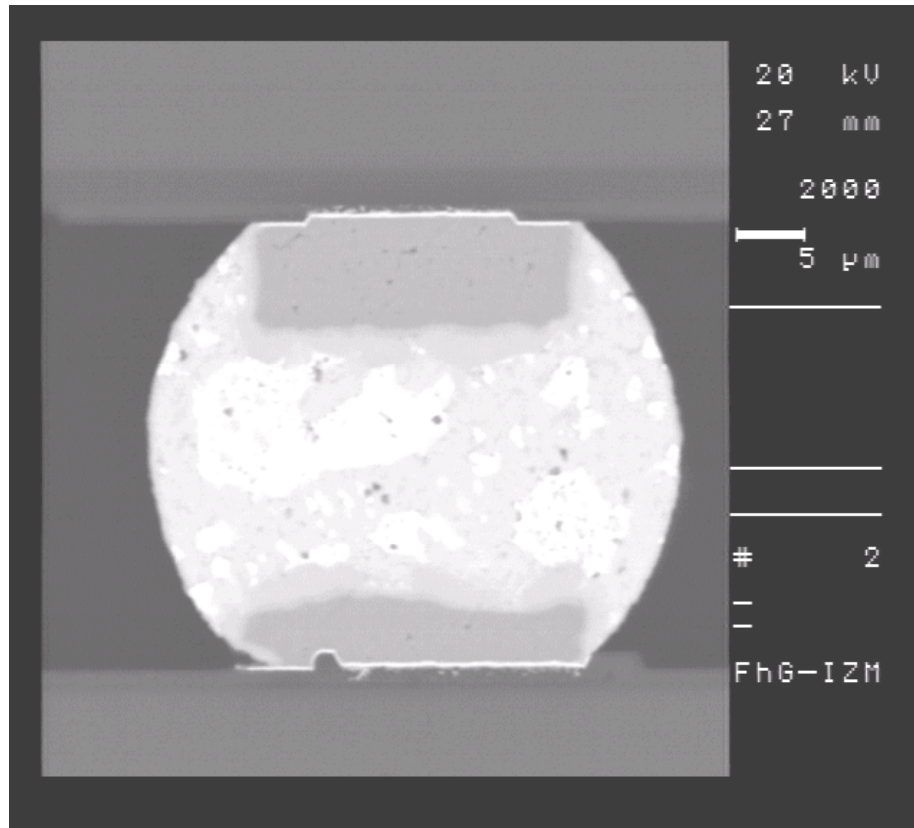
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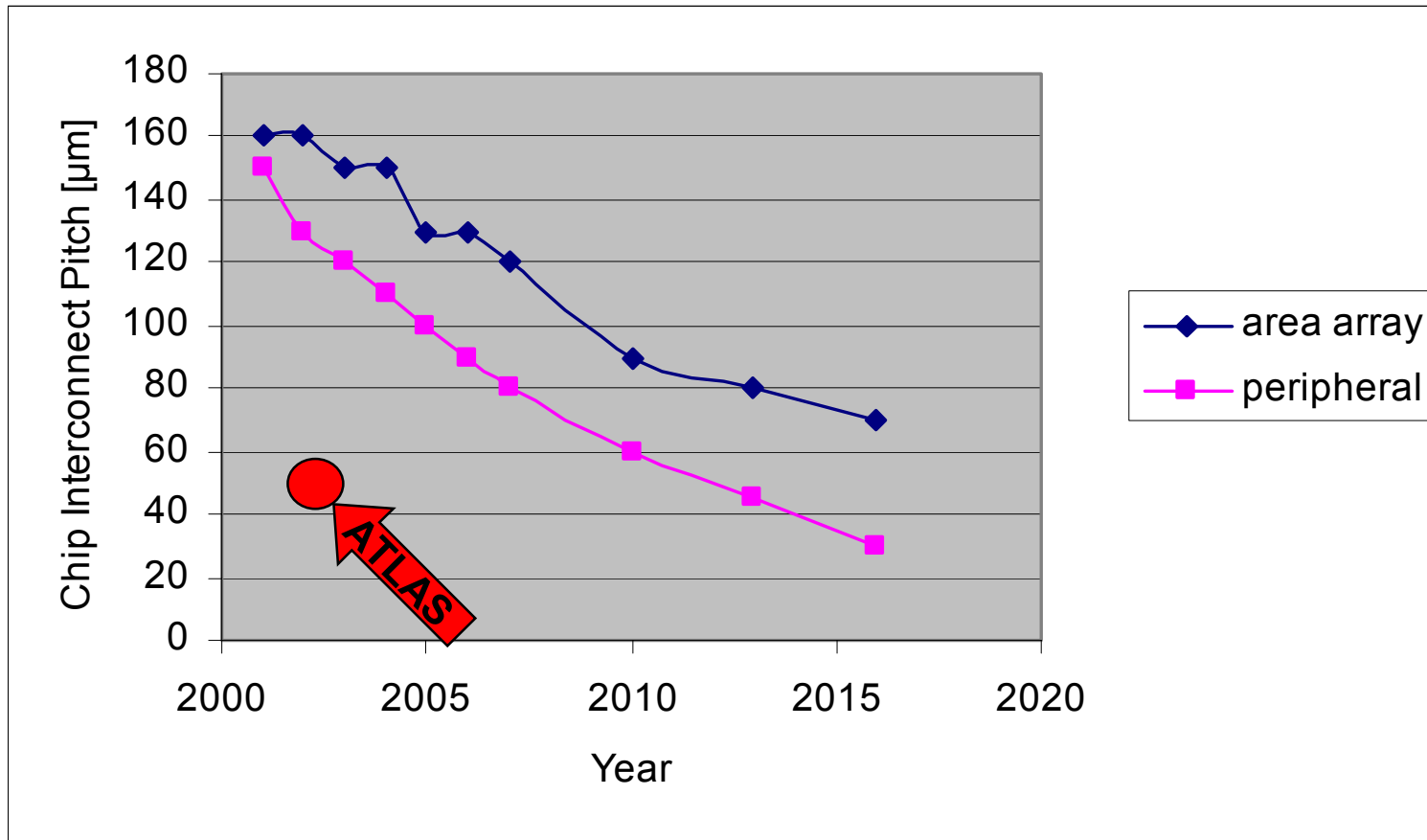
Defect Classes



Flip Chip Bonds

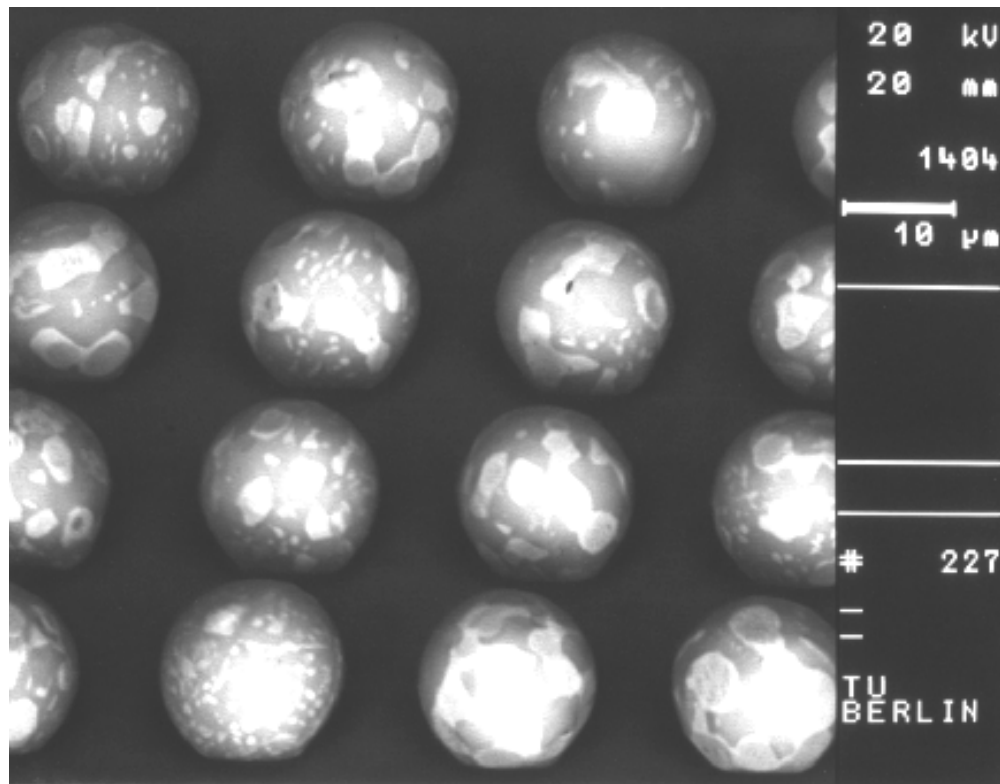


IC Technology Roadmap: Chip Interconnect Pitch



Source: ITRS

Future Requirements: Bump size and Pitch



Solder Bumping PbSn37/63

Diameter: 10 μm

Pitch: 20 μm



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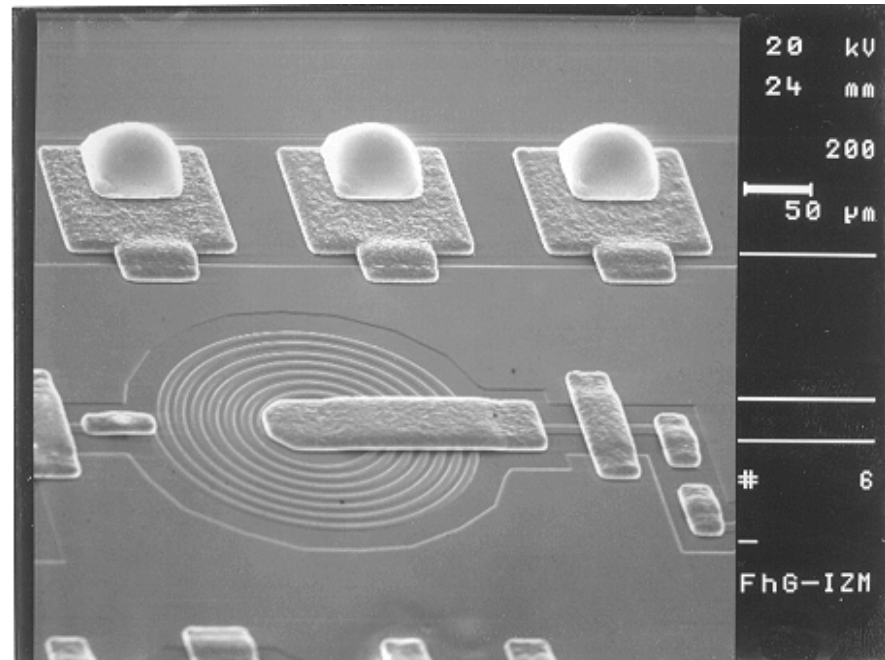
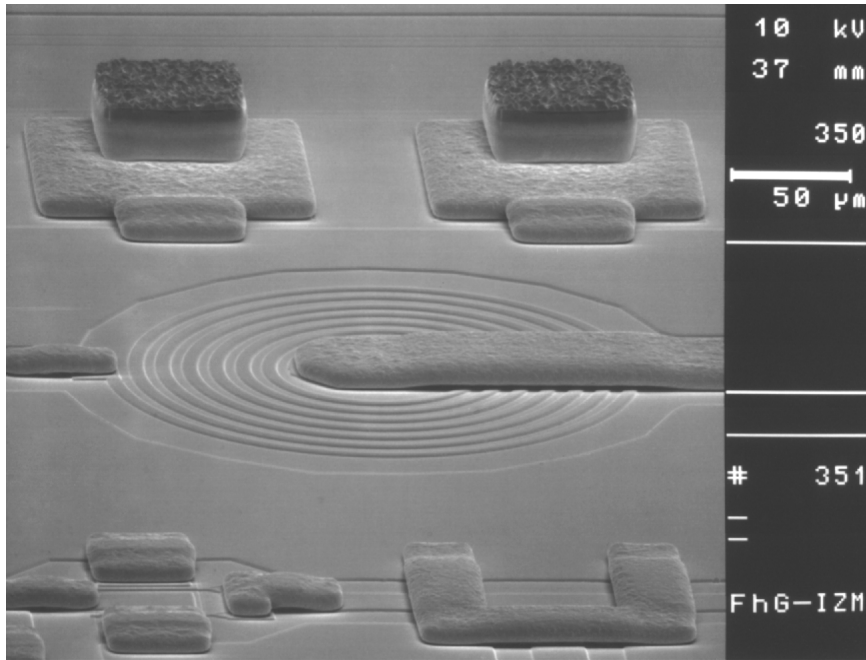
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Future Requirements: Lead Free

Solder for FC Interconnects		Melting Point
SnBi	42/58	138°C
PbSn	37/63	183°C
SnZn	91/9	199°C
SnAg	96.5/3.5	221°C
SnCu	99.3/0.7	227°C
AuSn	80/20	280°C
PbSn	95/5	314°C

Au-Sn Bumping on GaAs

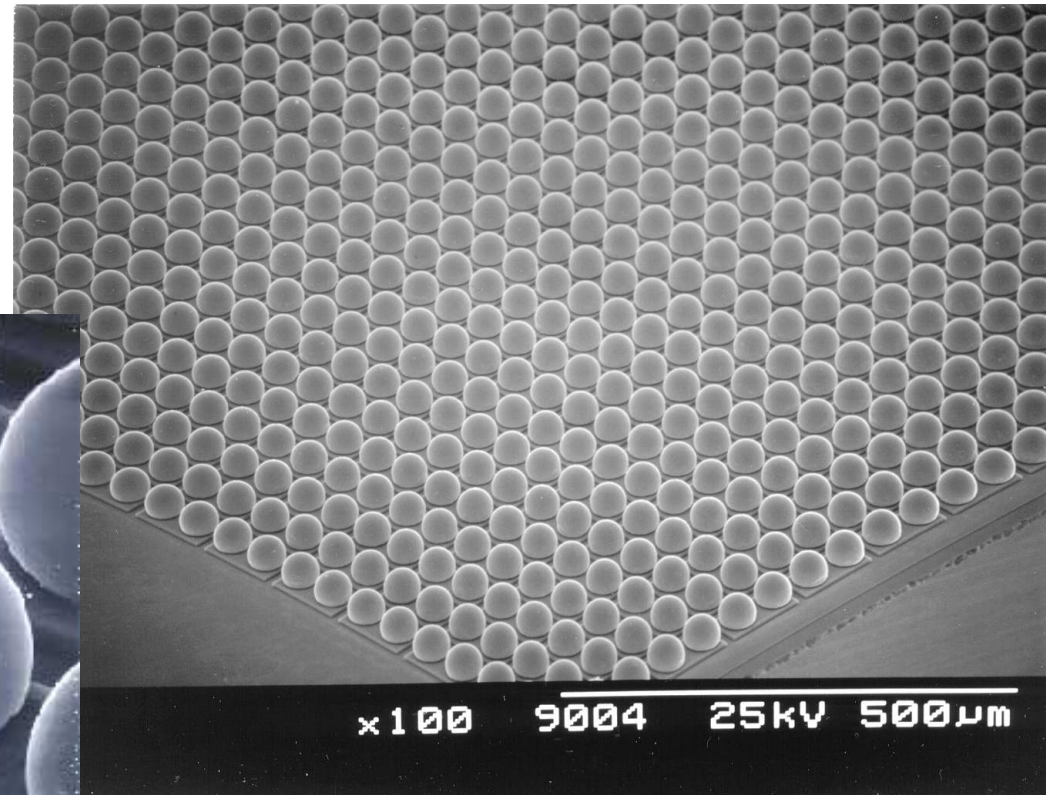
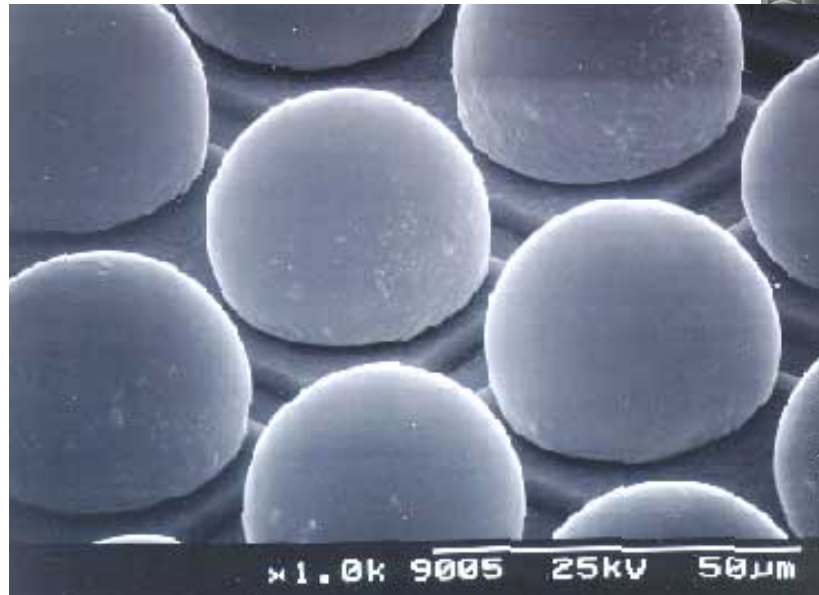


Au-Sn-Bumps - (48 x 48) μm^2
after Electroplating

Au-Sn-Bumps - (48 x 48) μm^2
after Reflow

AuSn Electroplated Bumps

- 50 μm pitch full array
- 30 μm AuSn20
- x-ray pixel detector



Lead Free Bumping

SnAg

Meeting the requirements of future environmentally friendly lead-free flip chip interconnects basing on the EU-directive ROHS 2000

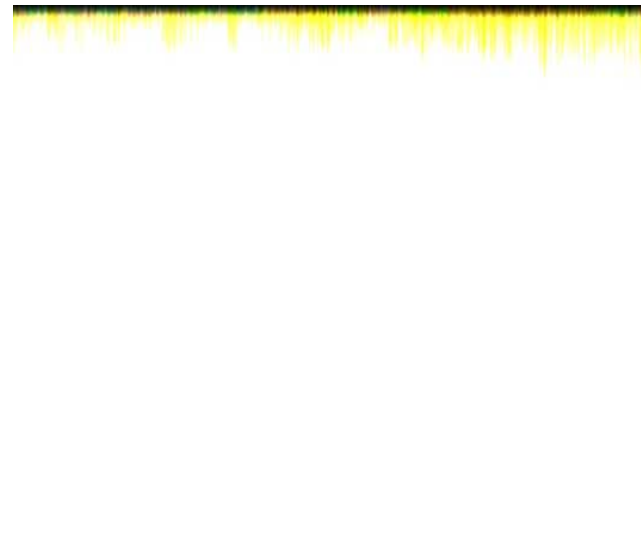
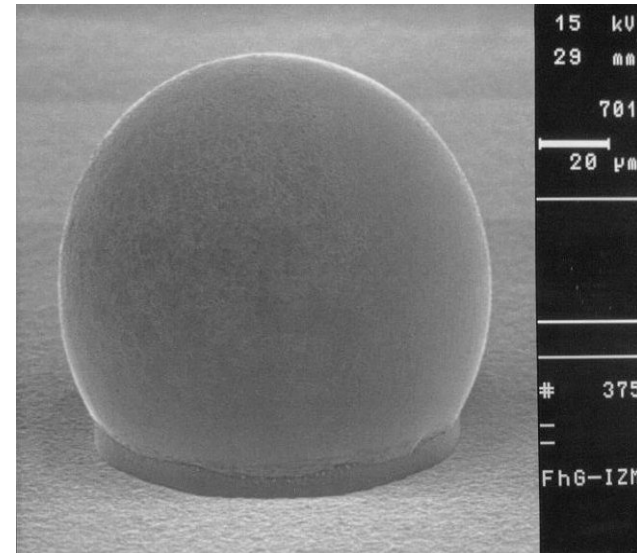
Bump dimensions

Size: 30 -100 μm

Pitch: down to 50 μm

Ag composition: 3.0 ~ 4.0 at. %

Melting point: 221 $^{\circ}\text{C}$



Future Requirements: Thin Silicon



Silicon becomes flexible when thickness is reduced down to less than 30µm

- **bending radius 1mm / 1µm thickness**
- **fully flexible and ultra thin systems available**
- **best opportunities to proceed with FC and CSP technologies**
- **basis for 3D chip integration**



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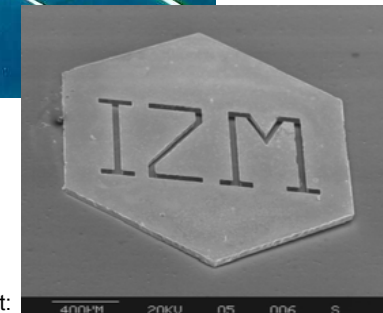
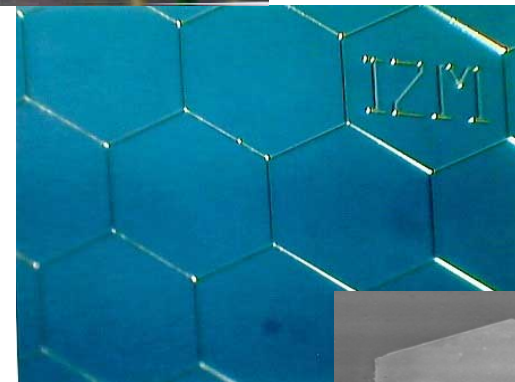
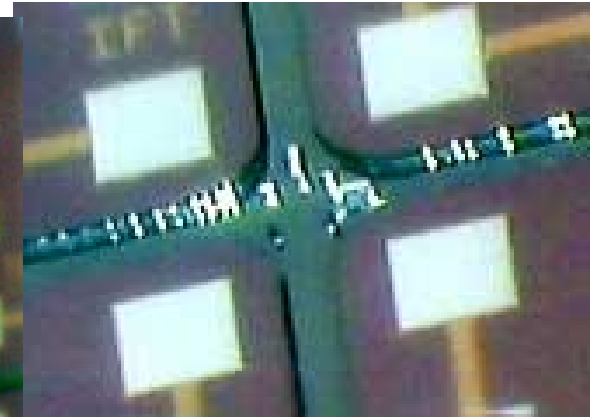
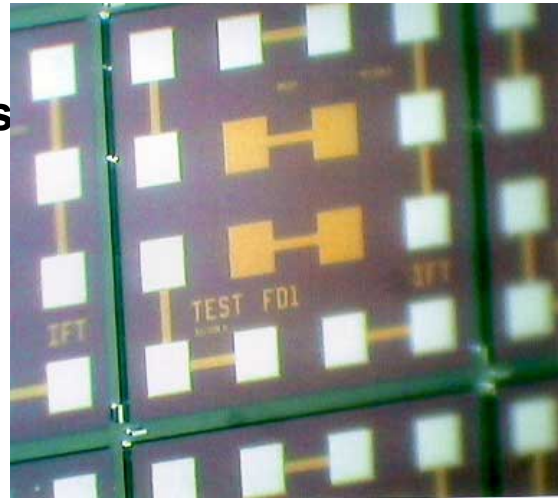
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Dicing by Thinning

- Dry Etching of about 30 μ m deep groves
- Backside Grinding - Etching - CMP
- nearly ideal chip edges (rounded corners are possible)
- shorter process times for singulation into individual chips
- narrow cuts save silicon area for small chips
- non rectangular dies are possible

Rounded chip corners



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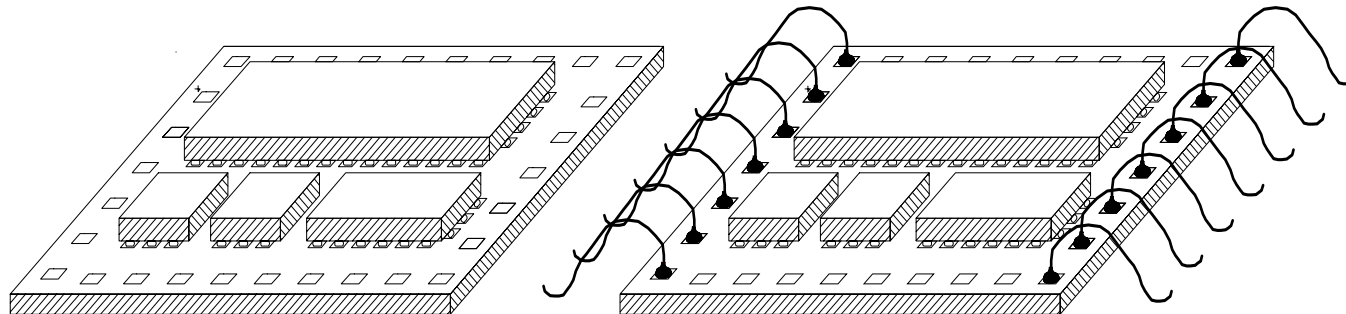
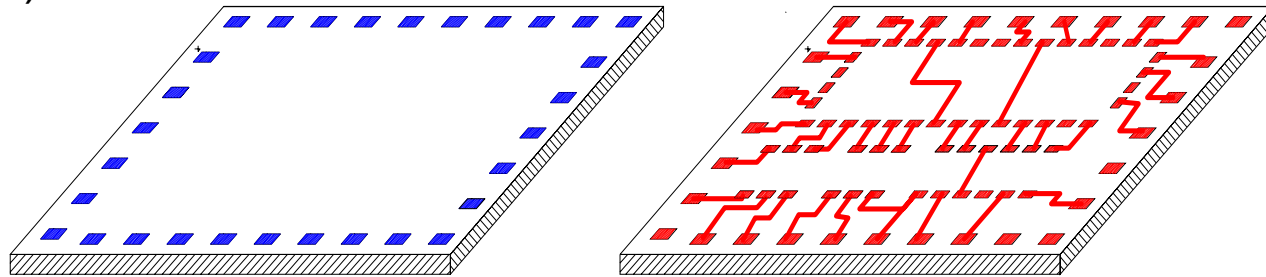
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Status of Silicon on Silicon Modules

base chip
(i.e. sensor)

redistribution
polymer / copper
(if required)



FC bonded
system chips

wire bonds to next
packaging level
(flex or pwb)



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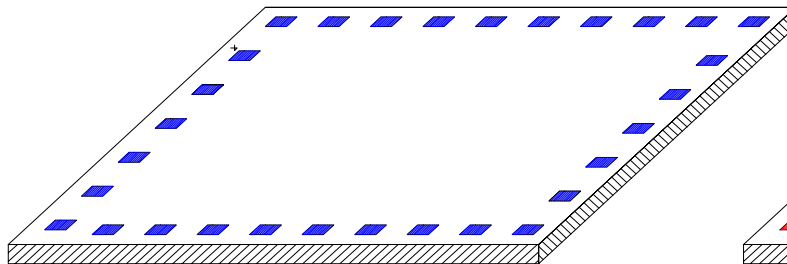


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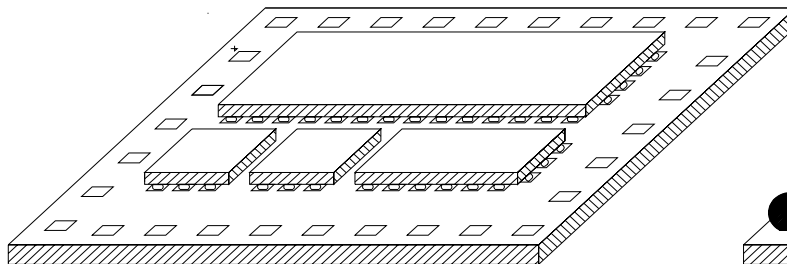
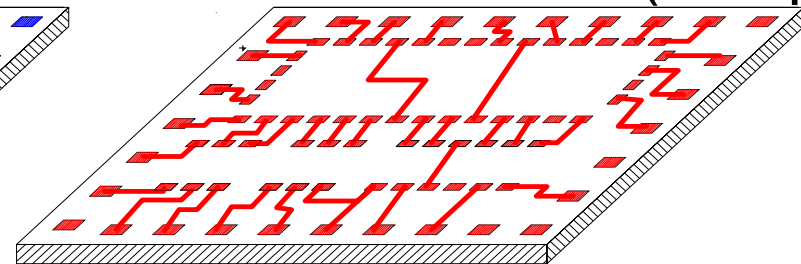
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Thin Dies help to avoid Wire Bonds

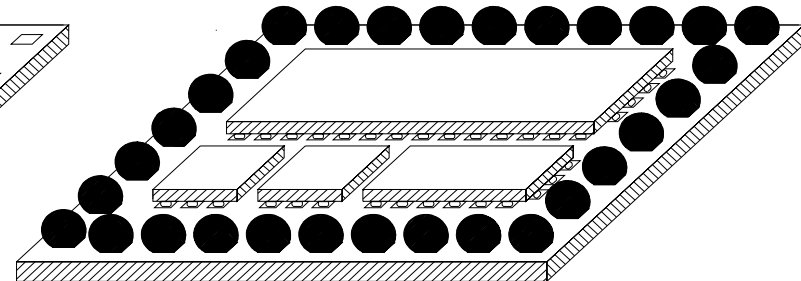
base chip



redistribution
polymer / copper
(if required)



FC bonded thinned
system chips

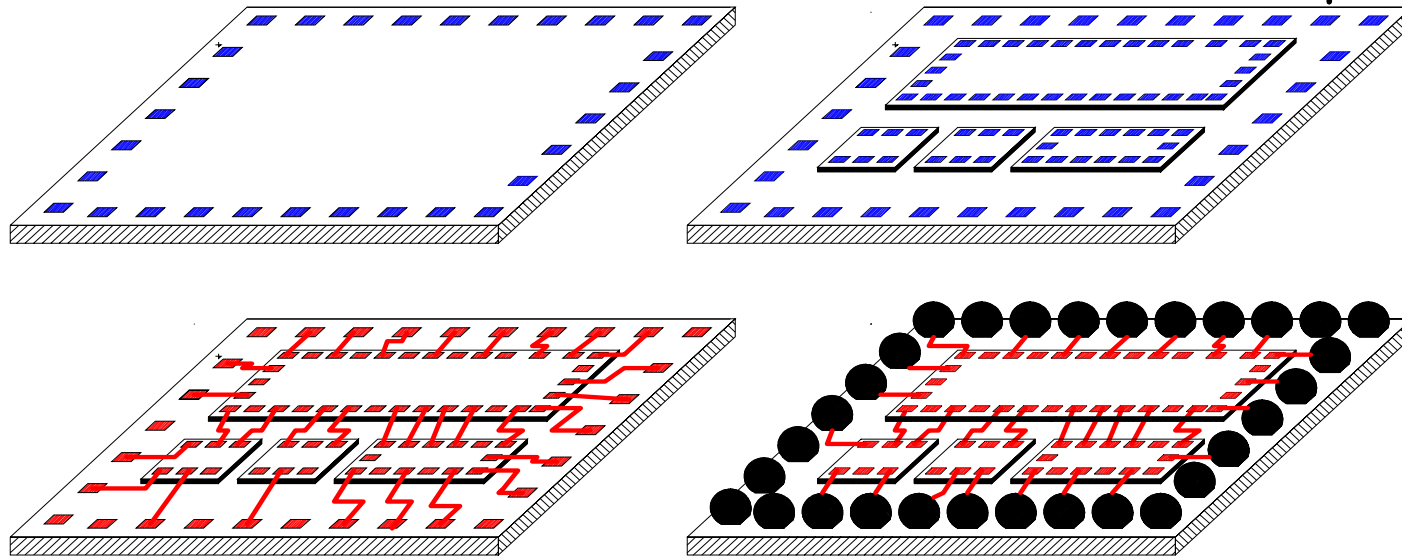


balls for interconnection
to the next packaging level
(flex)

Silicon on Silicon Modules with direct interconnectes Dies

Base Chip

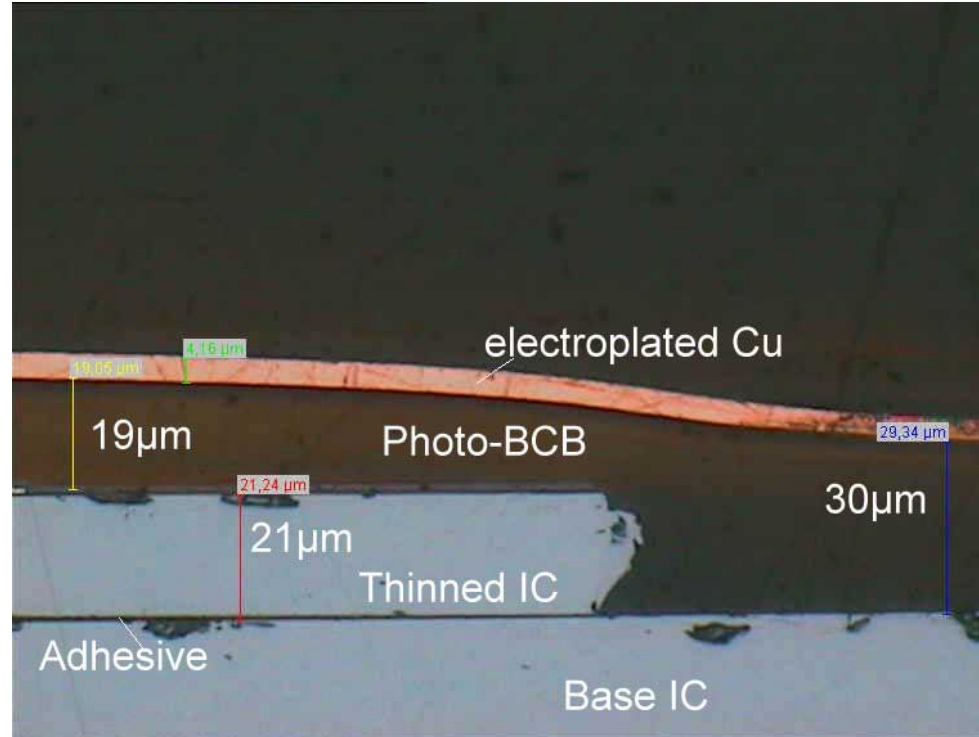
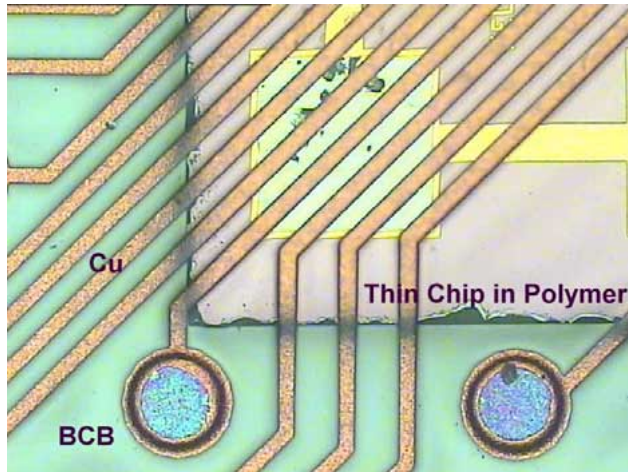
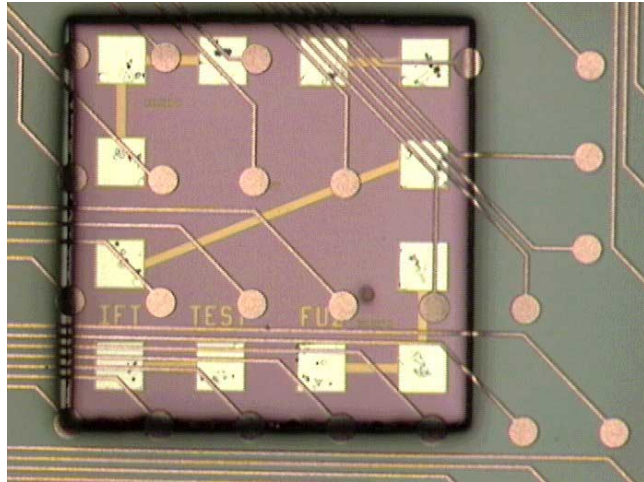
Mounting of
thinned Dies
 $d=20\mu\text{m}$



Redistribution
Polymer / Copper

Balls für
Boardmounting

Silicon on Silicon Modules with direct interconnectes Dies



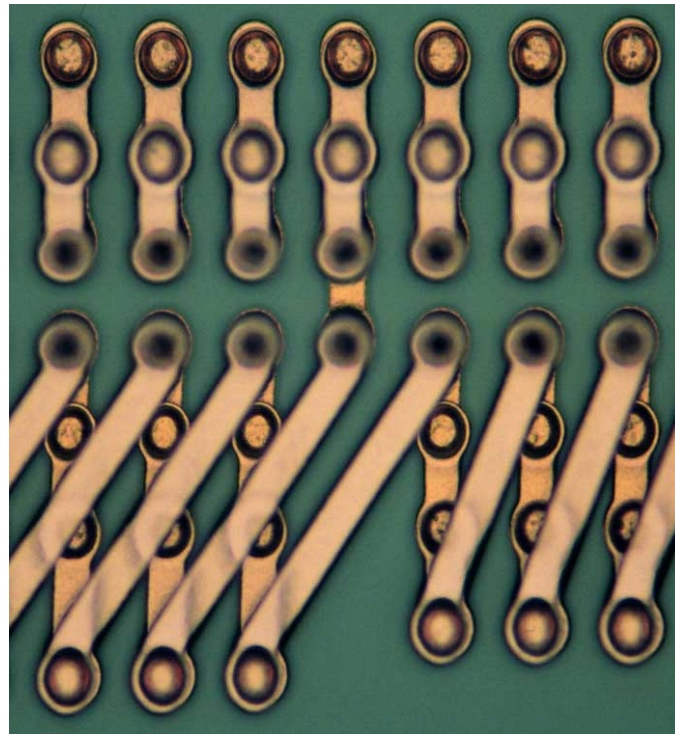
Reliability

passed 1000 cycles
-55°C / +125°C

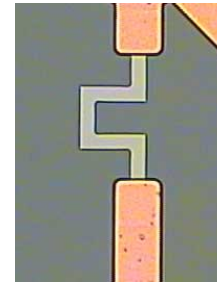
Future Requirements: Integration of Passive Components

**ATLAS
MCM - D**

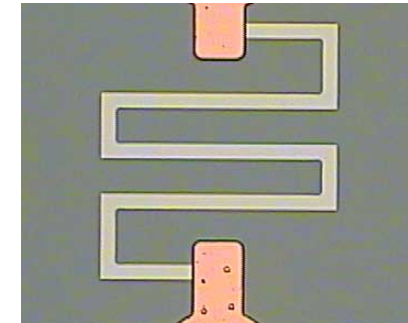
Si Substrate
**Multilayer of 5 metal
& 5 dielectric layers**
Dielectric:
Photo-BCB: 5 μm
Metallization:
Ti:W/Cu - ep. Cu (3 μm)



thinfilm resistors

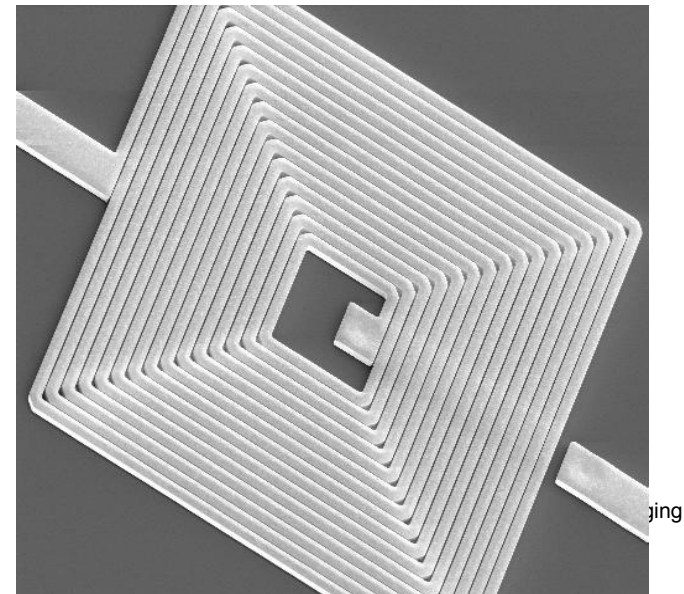


$R = 1k\Omega$



$R = 5k\Omega$

thinfilm inductors



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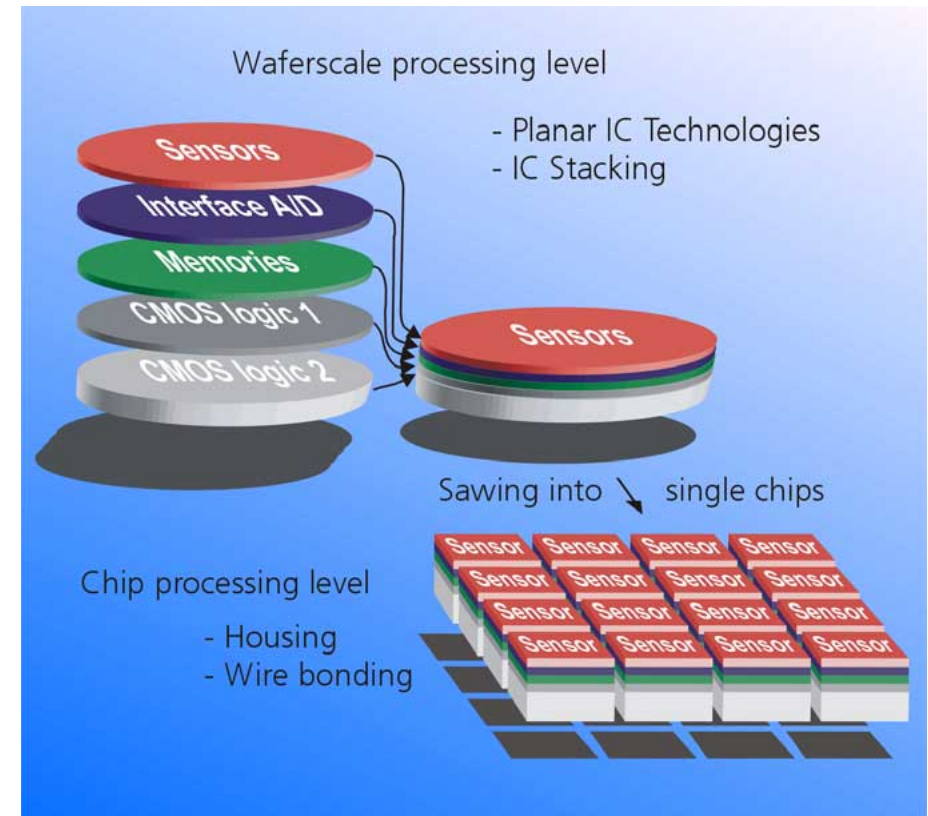
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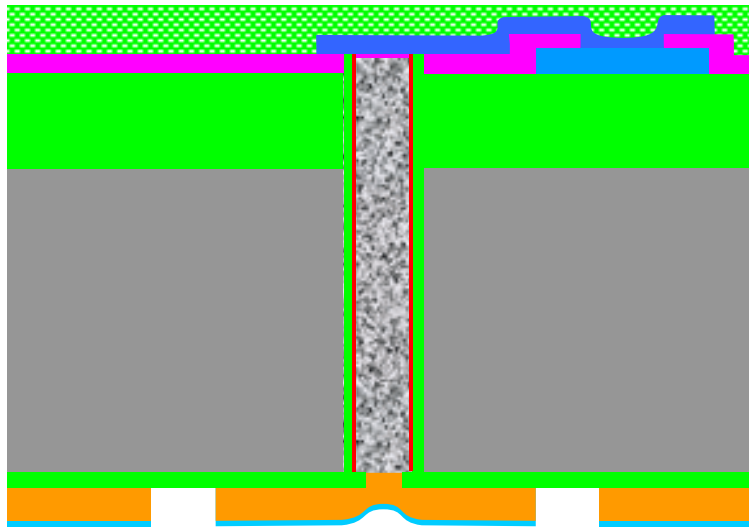
Future Requirements: 3D Integration: Vertical System Integration - VSI

- **Increased Performance**
 - Less wiring delay
 - More bits of memory / cm²
- **Combination of the advantages of different device technologies**
- **Portable Systems (minimum volume)**
- **Systems for high parallel signal processing**



Vertical System Integration InterChip Via Technology (ICV) / Soldering Concept

Top
Wafer



- Fabrication of Tungsten or Copper filled InterChip Vias on Top Substrate
- Via Opening and Metallization
- Thinning (20 μ m)
- Opening of Plugs
- Electroplating



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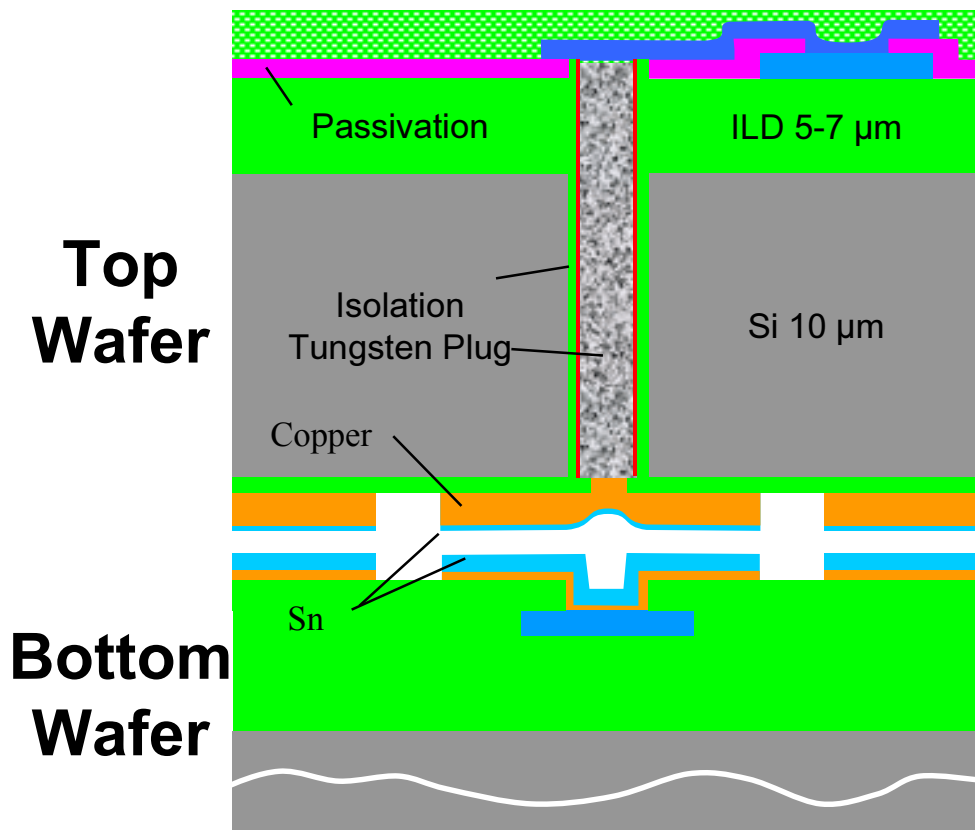
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Vertical System Integration InterChip Via Technology (ICV) / Soldering Concept



- Fabrication of Tungsten or Copper filled InterChip Vias on Top Substrate
- Via Opening and Metallization
- Thinning (20μm)
- Opening of Plugs
- Electroplating
- Alignment and Soldering



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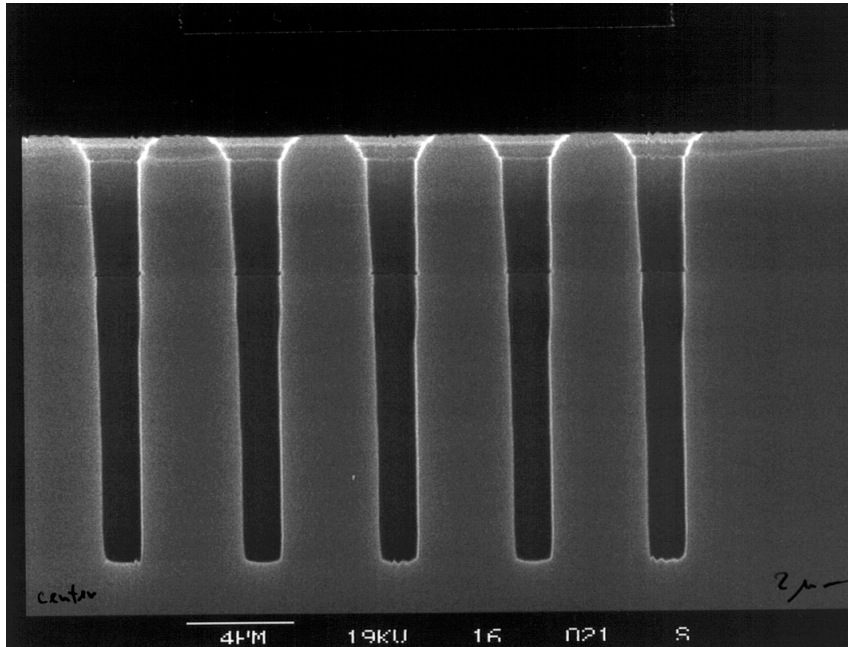
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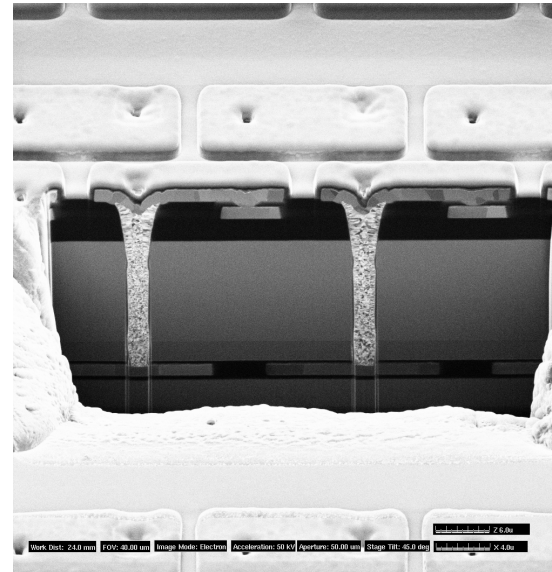
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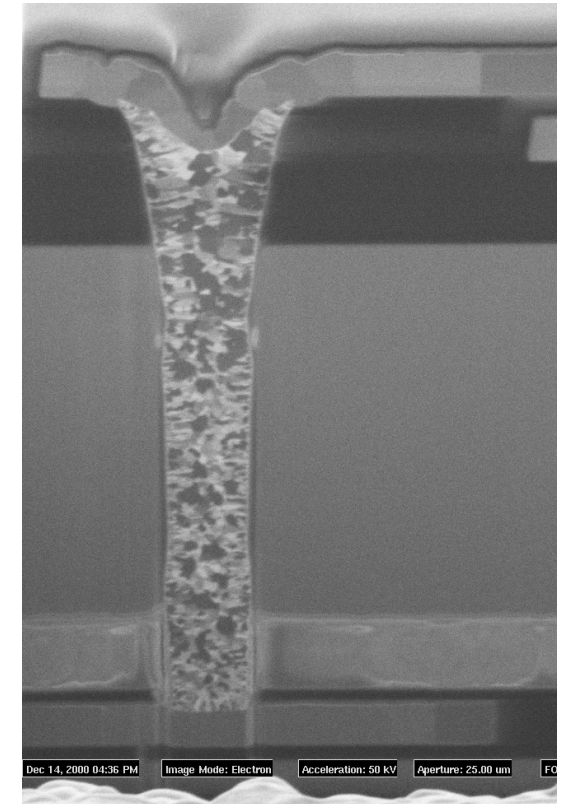
Vertical System Integration InterChip Via Technology (ICV) / Soldering Concept



Si Trench Etch



Cross section of a vertically integrated test chip structure, showing $2.5 \times 2.5 \mu\text{m}^2$ Tungsten-filled interchip vias (FIB)



thank you for your attention



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